

JUAN ANTONIO LOPEZ VILLANUEVA



Ficha del Directorio

Grupo de Investigación: GRUPO DE INVESTIGACION EN DISPOSITIVOS ELECTRONICOS (Cod.: TIC105)

Departamento: Universidad de Granada. Electrónica y Tecnología de Computadores

Citas en Google Scholar: <https://scholar.google.es/citations?user=9KKVSOAAAAAJ&hl=es>

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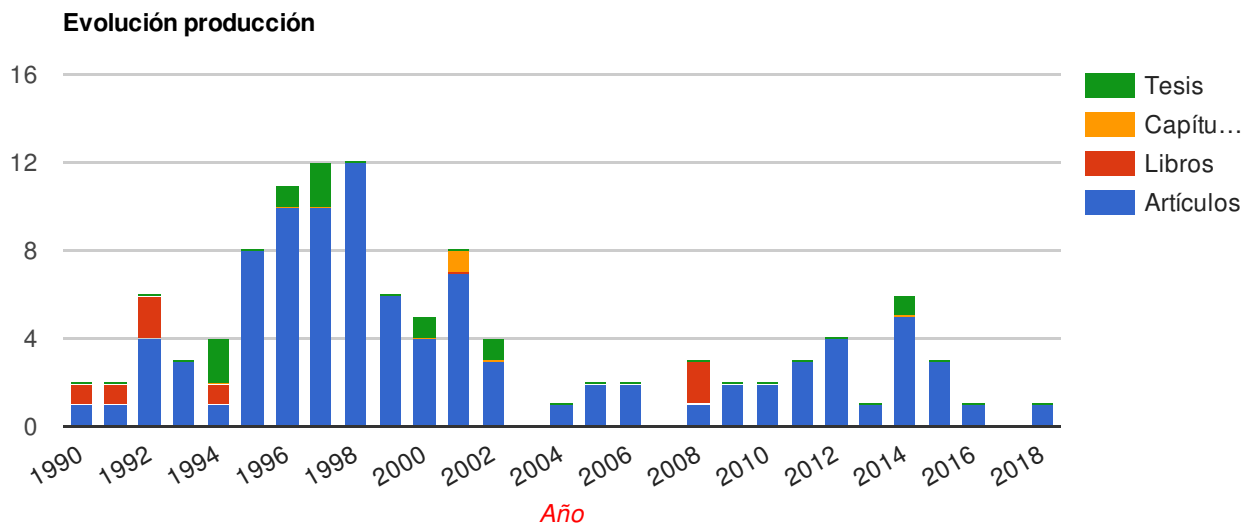
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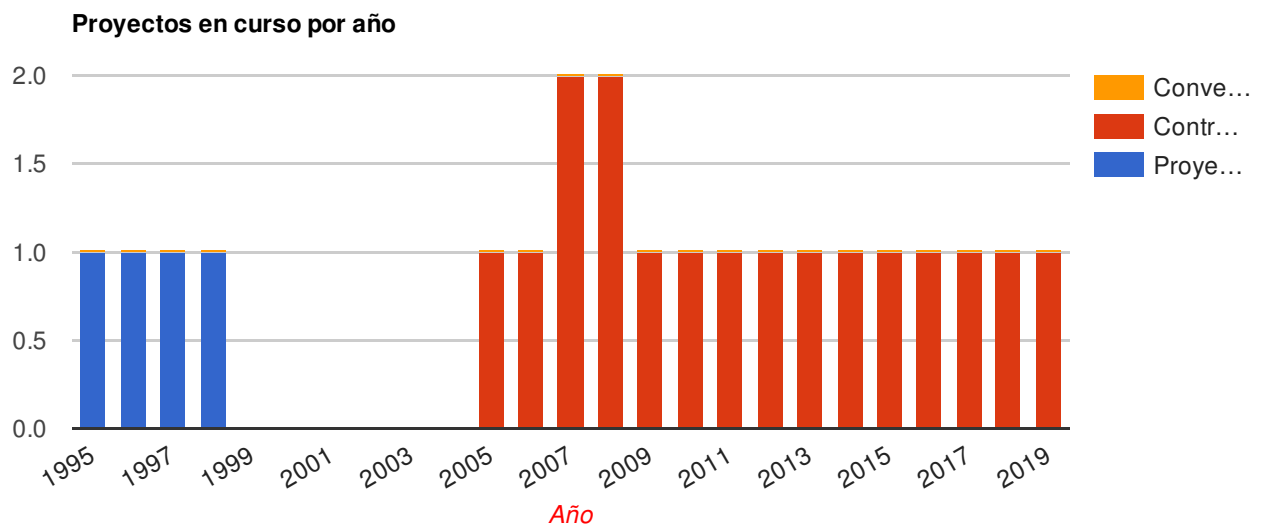
Producción 114

Artículos (98) Libros (7) Capítulos de Libros (1) Tesis dirigidas (8)



Proyectos dirigidos 3

Proyectos (1) Contratos (2) Convenios (0)



Actividades 0

Titulo publicación	Fuente	Tipo	Fecha
Asymmetric enhanced surface interdigitated electrode capacitor with two out-of-plane electrodes	Sensors and actuators b: chemical	Articulo	2018
Printed electrodes structures as capacitive humidity sensors: a comparison	Sensors and actuators a: physical	Articulo	2016
A printed capacitive-resistive double sensor for toluene and moisture sensing	Sensors and actuators b: chemical	Articulo	2015
Cantilever fabrication by a printing and bonding process	IEEE Journal of Microelectromechanical Systems	Articulo	2015
Improved manufacturing process for printed cantilevers by using water removable sacrificial substrate	Sensors and actuators a: physical	Articulo	2015
A novel electrode structure compared with interdigitated electrodes as capacitive sensor	Sensors and actuators b: chemical	Articulo	2014
Compact modelling and contact effects in thin film transistors	IEEE Transactions on Electron Devices	Articulo	2014
Design and characterization of a low thermal drift capacitive humidity sensor by inkjet-printing	Sensors and actuators b: chemical	Articulo	2014
Design of multisensor systems for environmental monitoring		Tesis doctoral	2014
Electrical characterization of controlled and unintentional modified metal-organic contacts	Organic electronics	Articulo	2014
Space-charge and injection limited current in organic diodes: a unified model	Organic electronics	Articulo	2014
Characterization of organic thin film transistors with hysteresis and contact effects	Organic electronics	Articulo	2013
Effects of gate oxide and junction nonuniformity on the dc and low-frequency noise performance of four-gate transistors	IEEE Transactions on Electron Devices	Articulo	2012
Effects of gate oxide and junction nonuniformity on the dc and low-frequency noise performance of four-gate transistors	IEEE Transactions on Electron Devices	Articulo	2012
Influence of size and shape of InAs/GaAs quantum dots in the photophysics of regimented arrays	Journal of Applied Physics	Articulo	2012
Modeling the transition from ohmic to space charge limited current in organic semiconductors	Organic electronics	Articulo	2012
Contact effects in compact models of organic thin film transistors: application to zinc phthalocyanine-based transistors	Organic electronics	Articulo	2011
Miniband structure and photon absorption in regimented quantum dot systems	Journal of Applied Physics	Articulo	2011
Thermal drift reduction with multiple bias current for MOSFET dosimeters	Physics in Medicine and Biology	Articulo	2011
Intraband photon absorption in edge-defined nanowire superlattices for optoelectronic applications	Journal of Applied Physics	Articulo	2010
Localization and quantification of noise sources in four-gate field-effect-transistors	International Journal of Numerical Modelling: Electronic Networks, Devices and Fields	Articulo	2010
Computational study of a nanoscopic fuse based on organic molecules	Proceedings of the 13th International Workshop on Computational Electronics 2009	Articulo	2009
On the application of periodic quantum wire nanostructures in optical sensors	Optica pura y aplicada	Articulo	2009
A low-frequency noise model for four-gate field-effect transistors	IEEE Transactions on Electron Devices	Articulo	2008
	Departamento de electrónica v		

Fundamentos de teoría de circuitos para electrónica	Departamento de electrónica y tecnología de computadores	Libros	2008
Problemas de electrónica básica	Departamento de electrónica y tecnología de computadores	Libros	2008
Determination of the concentration of recombination centers in thin asymmetrical p-n junctions from capacitance transient spectroscopy	Applied physics letters	Articulo	2006
Evaluation of a low-cost commercial mosfet as radiation dosimeter	Sensors and actuators a: physical	Articulo	2006
A simple model for analysing the effects of band non-parabolicity in nanostructures	Semiconductor science and technology	Articulo	2005
A solution of the effective-mass schro?dinger equation in general isotropic and nonparabolic bands for the study of two-dimensional carrier gases	Journal of applied physics	Articulo	2005
Effects of oxygen related defects on the electrical and thermal behavior of a n(+)-p junction	Journal of applied physics	Articulo	2004
Direct and trap-assisted elastic tunneling through ultrathin gate oxides	Journal of applied physics	Articulo	2002
Generation-recombination noise in highly asymmetrical p-n junctions	Journal of applied physics	Articulo	2002
Monte carlo simulation of electron mobility in silicon-on-insulator structures	Solid-state electronics	Articulo	2002
Sistema de telecontrol vía radio para plantas de helióstatos autónomos	Universidad de Málaga. ingeniería de comunicaciones	Tesis doctoral	2002
A simple subthreshold swing model for short channel mosfets	Solid-state electronics	Articulo	2001
Electron transport in silicon-on-insulator devices	Solid-state electronics	Articulo	2001
Electron transport in ultrathin double-gate soi devices	Microelectronic engineering	Articulo	2001
Foreword	Solid-state electronics	Articulo	2001
Monte carlo simulation of electron transport in silicon-on-insulator devices	Silicon on insulator. technology and devices x	Capítulo de libro	2001
Physical model for trap-assisted inelastic tunneling in metal-oxide-semiconductor structures	Journal of applied physics	Articulo	2001
Role of surface-roughness scattering in double gate silicon-on-insulator inversion layers	Journal of applied physics	Articulo	2001
Strained-si on si1-xgex mosfet inversion layer centroid modeling	IEEE transactions on electron devices	Articulo	2001
Deep submicrometer soi mosfet drain current model including series resistance, self-heating and velocity overshoot effects	IEEE electron device letters	Articulo	2000
Effects of the inversion-layer centroid on the performance of double-gate mosfet's	IEEE transactions on electron devices	Articulo	2000
Semiempirical closed-form models for the inversion-layer centroid of a p-mos including quantum effects	Semiconductor science and technology	Articulo	2000
Simulación y modelado de transistores mos de doble puerta	Universidad de Granada. electrónica y tecnología de computadoras	Tesis doctoral	2000
The escape time of electrons from localised states	Physica status solidi (b): basic research	Articulo	2000
A computational study of the strained-si mosfet: a possible alternative for the next century electronics industry	Computer physics communications	Articulo	1999
Electron mobility in extremely thin single-gate silicon-on-insulator inversion layers	Journal of applied physics	Articulo	1999
Experimental determination of the effective mobility in nmosfets: a comparative study	Solid-state electronics	Articulo	1999

Hole confinement and energy subbands in a silicon inversion layer using the effective mass theory	Journal of applied physics	Articulo	1999
Local larmor clock approach to the escape time	Physics letters a	Articulo	1999
Surface roughness at the si-sio2 interfaces in fully depleted silicon-on-insulator inversion layers	Journal of applied physics	Articulo	1999
2-dimensional drift-diffusion simulation of superficial strained-si/si1-xgex channel metal-oxide-semiconductor field-effect transistors		Articulo	1998
A beta-sic mosfet monte carlo simulator including inversion layer quantization	Vlsi design	Articulo	1998
A model for the drain current of deep submicrometer mosfet's including electron-velocity overshoot	ieee transactions on electron devices	Articulo	1998
An analytical model for the electron velocity overshoot effects in strained-si on sixge1-x mosfet's	ieee transactions on electron devices	Articulo	1998
Development of a method for determining the dependence of the electron mobility on the longitudinal-electric field in mosfets	Vlsi design	Articulo	1998
Electron-mobility in quantized beta-sic inversion-layers		Articulo	1998
Energy dependence of the effective mass in the envelope-function approximation	Physica. b, condensed matter	Articulo	1998
I-v and small signal parameters modelling of ultrasubmicron mosfets including the significant electron-velocity overshoot effects, which are enhanced at low temperature	Journal de physique iv	Articulo	1998
Low temperature mobility improvement in high-mobility strained-si/si1-xgex multilayer mosfets	Journal de physique iv	Articulo	1998
Monte carlo simulation of electron transport properties in extremely thin soi mosfet's	ieee transactions on electron devices	Articulo	1998
Monte carlo simulation of non-local transport effects in strained si on relaxed si1-xgex heterostructures	Vlsi design	Articulo	1998
Phonon-limited electron mobility in ultrathin silicon-on- insulator inversion layers	Journal of applied physics	Articulo	1998
A closed-loop evaluation and validation of a method for determining the dependence of the electron mobility on the longitudinal-electric field in mosfet's	ieee transactions on electron devices	Articulo	1997
A detailed simulation study of the performance of beta-silicon carbide mosfets and a comparison with their silicon counterparts	Semiconductor science and technology	Articulo	1997
A monte carlo study on electron mobility in quantized cubic silicon carbide inversion layers	Journal of applied physics	Articulo	1997
Effects of the inversion layer centroid on mosfet behavior	ieee transactions on electron devices	Articulo	1997
Electron transport properties of quantized silicon carbide inversion layers	Journal of electronic materials	Articulo	1997
Estudio de sistemas electronicos en potenciales unidimensionales. aplicacion a la estructura metal-aislante-semiconductor	Universidad de granada. electrónica y tecnología de computadoras	Tesis doctoral	1997
Modeling effects of electron-velocity overshoot in a mosfet	ieee transactions on electron devices	Articulo	1997
Quantum 2-dimensional calculation of time constants of random telegraph signals in metal-oxide-semiconductor structures	Physical review. b, condensed matter	Articulo	1997
Simulacion mediante el metodo de monte carlo y modelado del transporte electronico en transistores mos de canal corto	Universidad de granada. electrónica y tecnología de computadoras	Tesis doctoral	1997

Study of the effects of a stepped doping profile in short-channel mosfet's	IEEE transactions on electron devices	Artículo	1997
The dependence of the electron-mobility on the longitudinal electric-field in mosfets	Semiconductor science and technology	Artículo	1997
Understanding the improved performance of strained Si/Si _{1-x} Ge _x channel mosfets	Semiconductor science and technology	Artículo	1997
A monte carlo study on the electron-transport properties of high-performance strained-si on relaxed Si _{1-x} Ge _x channel mosfets	Journal of applied physics	Artículo	1996
A procedure for the determination of the effective mobility in an n-mosfet in the moderate inversion region	Solid-state electronics	Artículo	1996
Coulomb scattering in strained-silicon inversion layers on Si _{1-x} Ge _x substrates	Applied physics letters	Artículo	1996
Dependence of the electron mobility on the longitudinal electric field in mosfets	Semiconductor science and technology	Artículo	1996
Developpement d'un simulateur pour transistors a effet de champ en surface de canal tres court	Universidad abdelmalek essaadi. física	Tesis doctoral	1996
Electric field dependence of the electron capture cross section of neutral traps in SiO ₂	Journal of the electrochemical society	Artículo	1996
Electron velocity saturation in quantized silicon carbide inversion layers	Applied physics letters	Artículo	1996
Influence of the doping profile on electron mobility in a mosfet	IEEE transactions on electron devices	Artículo	1996
Low-temperature modelling of electron-velocity-overshoot effects on 70-250 nm gate-length mosfets	Journal de physique iv	Artículo	1996
Semi-empirical model of electron mobility in mosfets in strong inversion regime	IEEE proceedings. circuits, devices and systems	Artículo	1996
Strained Si/SiGe heterostructures at low temperatures. a monte carlo study	Journal de physique iv	Artículo	1996
A model for the quantized accumulation layer in metal-insulator-semiconductor structures	Solid-state electronics	Artículo	1995
Comprehensive monte-carlo simulation of the nonradiative carrier capture process by impurities in semiconductors	Journal of applied physics	Artículo	1995
Effects of bulk-impurity and interface-charge on the electron-mobility in mosfets	Solid-state electronics	Artículo	1995
Electron trapping and detrapping in near-interfacial traps during Fowler-Nordheim tunneling injection at 77 K	Microelectronic engineering	Artículo	1995
Influence of the oxide-charge distribution profile on electron-mobility in mosfets	IEEE transactions on electron devices	Artículo	1995
Monte-carlo study of the statistics of electron-capture by shallow donors in silicon at low-temperatures	Physical review. B, condensed matter	Artículo	1995
Oxide charge space correlation in inversion-layers. 2. 3-dimensional oxide charge-distribution	Semiconductor science and technology	Artículo	1995
Universality of electron-mobility curves in mosfets - a monte-carlo study	IEEE transactions on electron devices	Artículo	1995
A comprehensive model for coulomb scattering in inversion-layers	Journal of applied physics	Artículo	1994
Análisis y modelización de la movilidad en transistores MOS	Departamento de electrónica y tecnología de computadores	Libros	1994
Estudio de las propiedades de transporte de electrones en láminas de inversión semiconductoras por el método de monte carlo	Universidad de Granada. electrónica y tecnología de computadoras	Tesis doctoral	1994
	Universidad de Granada		

Estudio experimental de la movilidad de los electrones en transistores metal-oxido-semiconductor	Universidad de Granada, electrónica y tecnología de computadoras	Tesis doctoral	1994
Accurate determination of silicon inversion layer mobility by the monte carlo method	Simulation of semiconductor devices and processes	Articulo	1993
An analytical expression for phonon limited mobility in silicon inversion layers	Journal of applied physics	Articulo	1993
Influence of the interface-state density on the electron mobility in silicon inversion layers	Journal of electronic materials	Articulo	1993
A high-frequency bidirectional capacitance method to study the evolution of the interface state density generated at low temperatures	Solid-state electronics	Articulo	1992
A non destructive method to determine impurity profiles in non-abrupt p-n junctions with deep levels	Solid-state electronics	Articulo	1992
Comportamiento eléctrico de uniones p+-n no abruptas con centros profundos	Departamento de electrónica y tecnología de computadores	Libros	1992
Efecto de la densidad de carga superficial sobre la movilidad efectiva en mosfet	Departamento de electrónica y tecnología de computadores	Libros	1992
Evolution of electrical magnitudes in gradual p-n junctions with deep levels during the emission of majority carriers	Journal of applied physics	Articulo	1992
Importance of the choice of the profile model for a p-n junction in the location of the deep levels	Journal of electronic materials	Articulo	1992
Analysis of the effects of constant current fowler-nordheim tunneling injection with charge-trapping inside the potential barrier	Journal of applied physics	Articulo	1991
Degradación del sistema si-sio2 producida por inyección fowler-nordheim	Departamento de electrónica y tecnología de computadores	Libros	1991
Analisis of a reverse-biased linear graded junction with high concentration of deep impurities	Solid-state electronics	Articulo	1990
Influencia de los niveles creados por el platino en una unión gradual lineal	Departamento de electrónica y tecnología de computadores	Libros	1990

	Título proyecto	Tipo	Inicio	Fin
1	Realización de un simulador bidimensional de celulas solares multiunión basadas en semiconductores iii-v para sistemas de concentración	Contrato	11/22/05	7/31/08
2	Modelización de transistores mos para aplicaciones analógicas	Proyecto	7/1/95	7/1/98
3	Realización de un simulador bidimensional de células solares multiunión basadas en semiconductores iii-v para sistemas de concentració15	Contrato	3/20/07	

Actividades 0

Título actividad	Fuente	Tipo	Fecha
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- ALBERTO JOSE PALMA LOPEZ (22)
- PEDRO CARTUJO CASSINELLO (19)
- JESUS BANQUERI OZAEZ (18)
- SALVADOR RODRIGUEZ BOLIVAR (17)
- FRANCISCO MANUEL GOMEZ CAMPOS (10)
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- ALMUDENA RIVADENEYRA TORRES (7)
- JOSÉ FERNÁNDEZ SALMERÓN (7)
- LUIS FERMÍN CAPITÁN VALLVEY (7)
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